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Supplementary information

Dual-field plated $\beta\mbox{-}Ga_2O_3$ nano-FETs with an off-state breakdown voltage exceeding

400 V

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Fig. S1 (a) Simulation results of electric-field distribution at different β -Ga₂O₃ thickness and (b) simulation results of breakdown voltage of the β -Ga₂O₃ nano-FETs at varying β -Ga₂O₃ thickness.



Fig. S2 (a, b) Optical microscope images and (c) AFM image of the dual-field plated β -Ga₂O₃ nano-FETs. (d, e) DC output and (f) off-state three-terminal hard breakdown measurement of the dual-field plated β -Ga₂O₃ nano-FET.